

HiPerFET™

Power MOSFETs

Single Die MOSFET

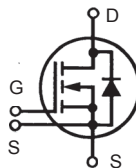
IXFN 34N100

$$V_{DSS} = 1000V$$

$$I_{D25} = 34A$$

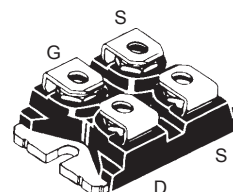
$$R_{DS(on)} = 0.28\Omega$$

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$; $R_{GS} = 1 M\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$, Chip capability	34	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	136	A
I_{AR}	$T_C = 25^\circ C$	34	A
E_{AR}	$T_C = 25^\circ C$	64	mJ
E_{AS}	$T_C = 25^\circ C$	4	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 A/\mu s$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$, $R_G = 2 \Omega$	5	V/ns
P_D	$T_C = 25^\circ C$	700	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
V_{ISOL}	50/60 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s	2500 3000	V~ V~
M_d	Mounting torque Terminal connection torque	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source
D = Drain
TAB = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard packages
- miniBLOC, with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

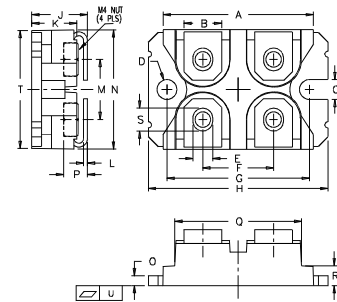
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ C$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 V$, $I_D = 3$ mA	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8$ mA	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 20 V_{DC}$, $V_{DS} = 0$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0 V$			100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu s$, duty cycle $d \leq 2\%$		0.25	0.28 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 15\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	18	40	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9200	pF
C_{oss}			1200	pF
C_{rss}			300	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		41	ns
t_r			65	ns
$t_{d(off)}$			110	ns
t_f			30	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		380	nC
Q_{gs}			65	nC
Q_{gd}			185	nC
R_{thJC}			0.05	0.18 K/W
R_{thCK}				K/W

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			34 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			136 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.3 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$ $T_J = 25^\circ\text{C}$	180		ns
Q_{RM}		330		ns
I_{RM}		2		μC
		8		A

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

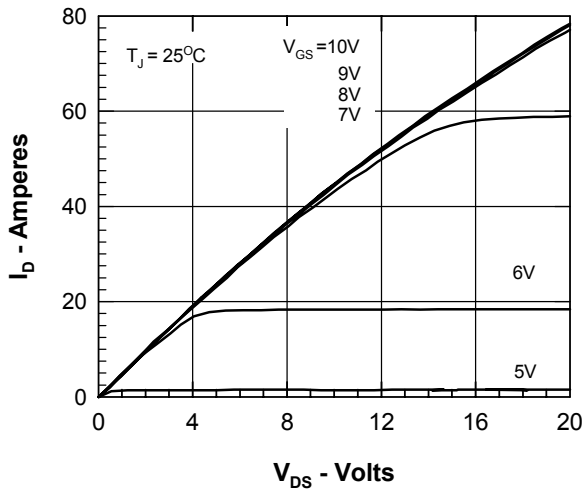


Figure 1. Output Characteristics at 25°C

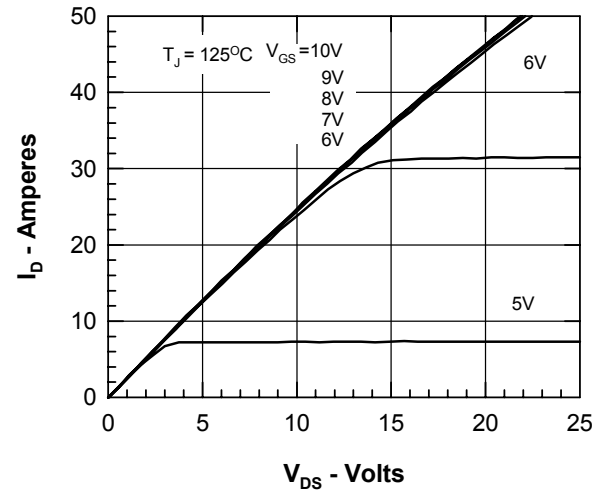


Figure 2. Output Characteristics at 125°C

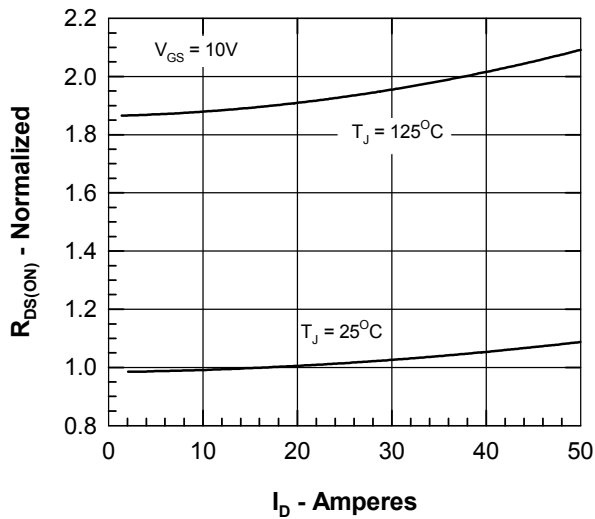


Figure 3. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. I_D

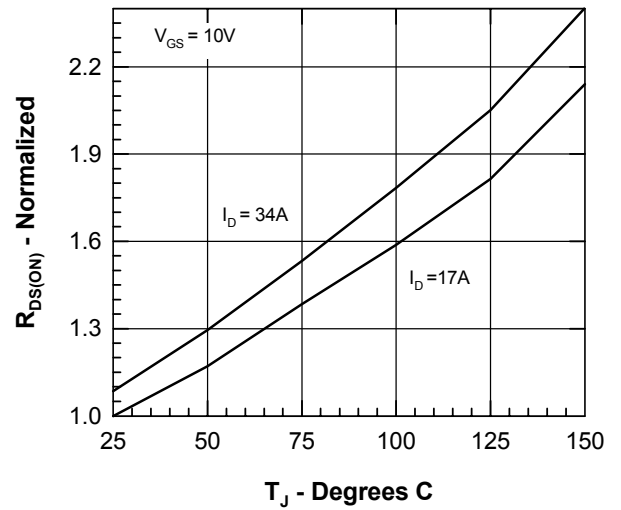


Figure 4. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. T_J

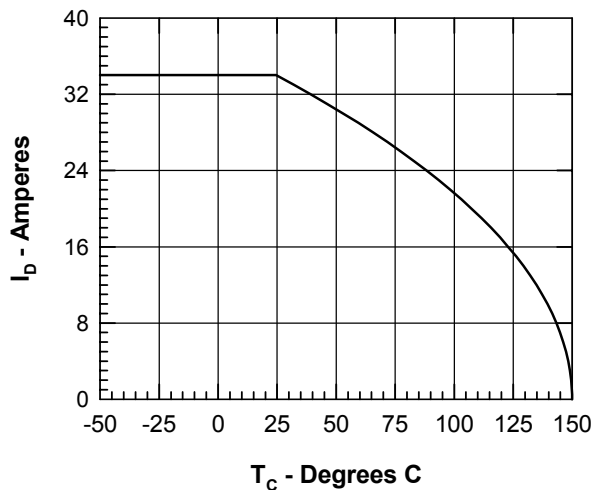


Figure 5. Drain Current vs. Case Temperature

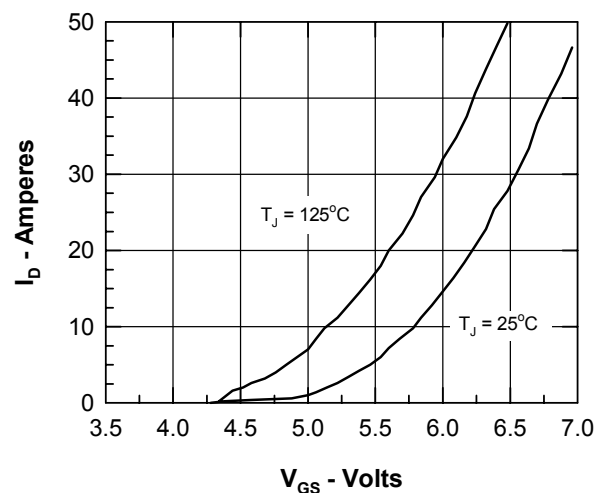
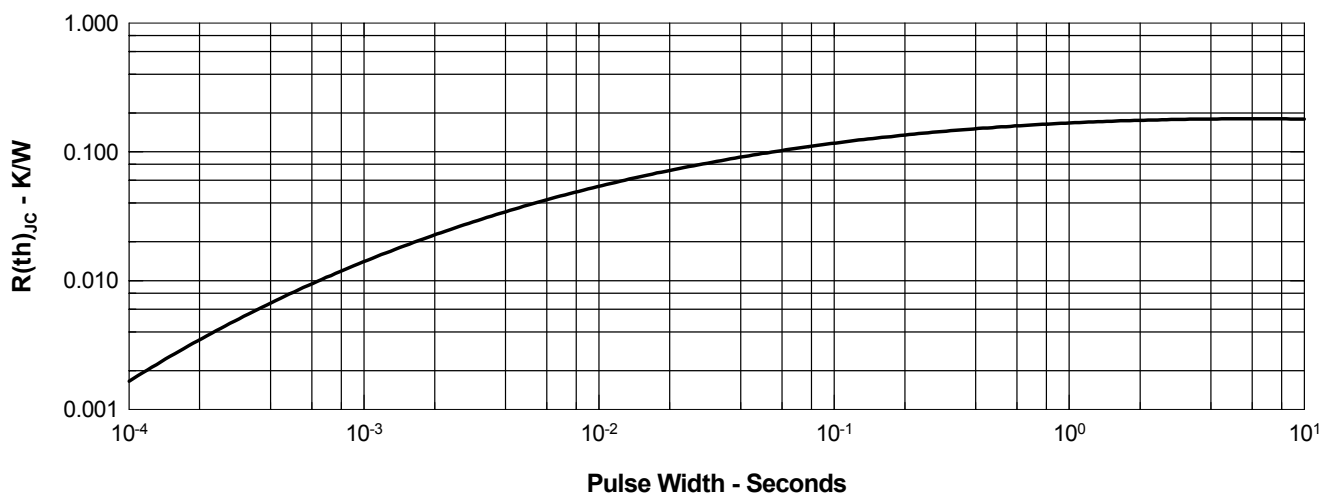
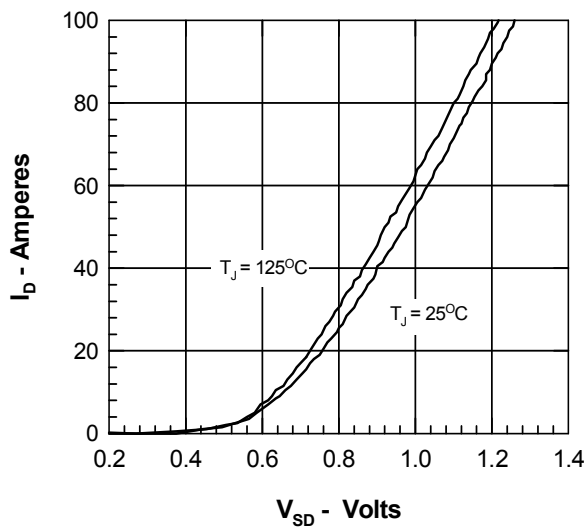
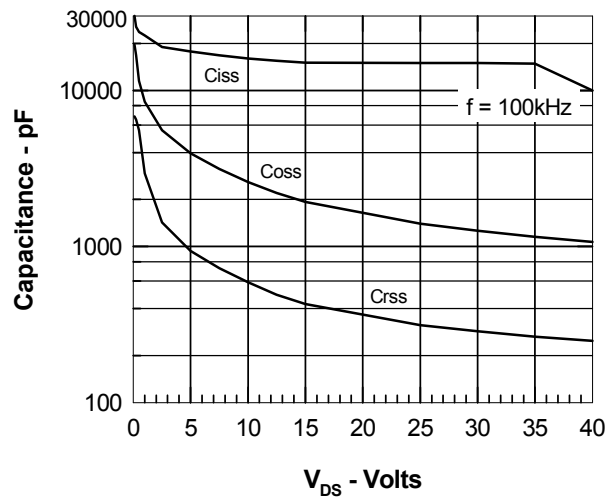
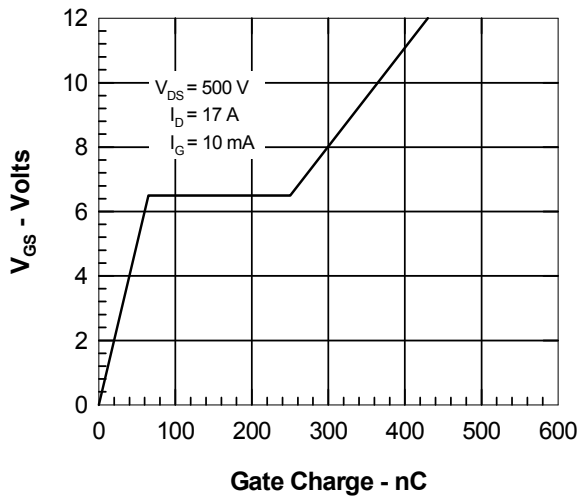


Figure 6. Admittance Curves



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343

AMEYA360

Components Supply Platform

Authorized Distribution Brand :



Website :

Welcome to visit www.ameya360.com

Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd
Minhang District, Shanghai , China

➤ Sales :

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

➤ Customer Service :

Email service@ameya360.com

➤ Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com